

Silicon ON INSULATOR Wafer

Product Description

SOI wafer (Silicon-on-Insulator) for a variety of application including MEMS , Power device , Pressure sensors and CMOS integrated circuit fabrication . SOI wafer provide a potential solution for high speed and low power consumption device and has been widely acknowledged as a new solution for high voltage and RF components. SOI wafer is a sandwich structure including a device layer (active layer) on top , a buried oxide layer (insulating SiO₂ layer) in the middle , and a handle wafer (bulk silicon) in the bottom .

- Totally customized
- Low and medium volumes
- Any diameter
- Any orientations
- Any thickness

Typical Properties

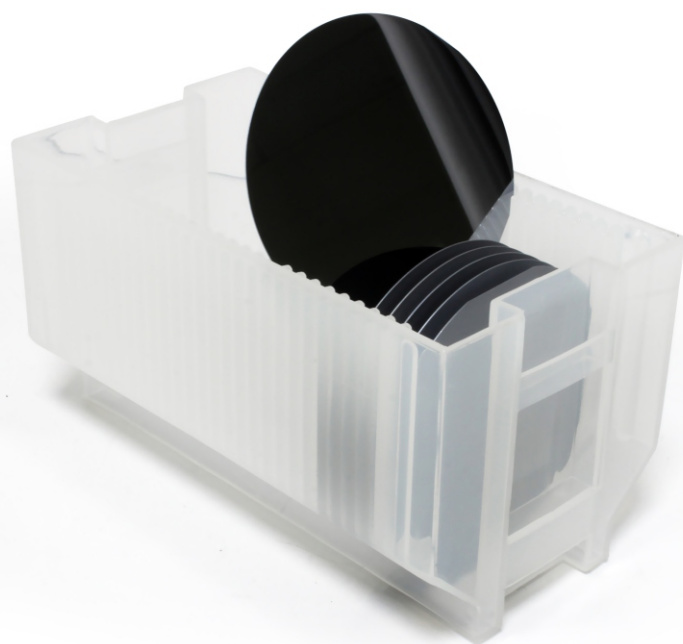
Dopant	:	Phosphorus
Crystal Orientation	:	< 100>
Type	:	N
CZ Resistance	:	1 to 150mΩ.cm
Resistivity	:	1.0-5.0Ω.cm
STIR	:	<2μm
Bow	:	30μm

Applications

- ✓ Silicon on insulator (SOI) wafer is used in silicon photonics.
- ✓ Silicon on insulator (SOI) wafer is used in microelectronic devices.
- ✓ Silicon on insulator (SOI) wafer is used for radio frequency (RF).
- ✓ High isolation, high linearity and electro-static discharge (ESD) tolerance

Key Features

Product	:	SOI Wafer
Stock No	:	NS6130-10-1308
CAS	:	7440-21-3
Diameter	:	4" (100mm)
Thickness	:	450μm



NS6130-10-1308

4"
Inch
N Type

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